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View Online at https://aerobasegroup.com/nsn/5961-01-309-6860
Inclosure Material:
Metal
Overall Length:
Between 0.160 inches and 0.180 inches
Terminal Length:
Between 0.500 inches and 0.750 inches
Overall Diameter:
Between 0.335 inches and 0.370 inches
Internal Configuration:
Field effect
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
To-205af
Electrode Internally-electrically Connected To Case:
Drain
Mounting Method:
Terminal
Terminal Circle Diameter:
0.200 inches
Features Provided:
Quality assurance level tx and electrostatic sensitive
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
100.0 drain to source voltage and 100.0 drain to gate voltage and 10.0 gate to source voltage
Current Rating Per Characteristic:
5.00 amperes off-state current, peak
Power Rating Per Characteristic:
8.33 watts total power dissipation
Maximum Operating Tempurature Per Measurement Point:
150.0 degrees celsius junction
Test Data Document:
81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Terminal Type And Quantity:
3 uninsulated wire lead
Specification Data:
81349-mil-s-19500/570 government specification
Shelf Life:
N/a
Unit Of Measure:

No

Demilitarization:

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